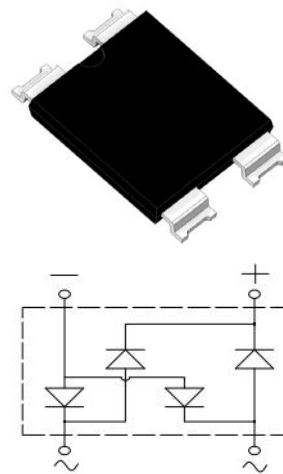


Bridge Rectifier Diode 整流桥

■Features 特点

Glass passivated chip junction 玻璃钝化结
High surge current capability 高浪涌电流能力
Ideal for Automated Placement 适用于平放
Peak Soak Temperature 260℃ 峰值浸润温度 260 度
Polarity 极性:as marked on body 见体标
Package 封装:YBS6



■Maximum Rating 最大额定值

(T_A=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

Characteristic 特性参数	Symbol 符号	YBSN 100005	YBSN 10001	YBSN 10002	YBSN 10004	YBSN 10006	YBSN 10008	YBSN 10010	Unit 单位
Device Marking Code 产品标码		YBSN 100005	YBSN 10001	YBSN 10002	YBSN 10004	YBSN 10006	YBSN 10008	YBSN 10010	
Peak Reverse Voltage 反向峰值电压	V _{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	V _{R(DC)}	50	100	200	400	600	800	1000	V
RMS Reverse Voltage RMS 反向电压	V _{R(RMS)}	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I _F	10							A
Peak Surge Current 峰值浪涌电流	I _{FSM}	250							A
Thermal Resistance J-A 结到环境热阻	R _{θJA}	50							℃/W
Junction and Storage Temperature 结温和储藏温度	T _J , T _{stg}	150℃, -55to+150℃							

■Electrical Characteristics 电特性

(T_A=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	V _F		1.0		V	I _F =10A
Reverse Current 反向电流	I _R			5	uA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _D		82		pF	V _R =4V, f=1MHz

■ Typical Characteristic Curve 典型特性曲线

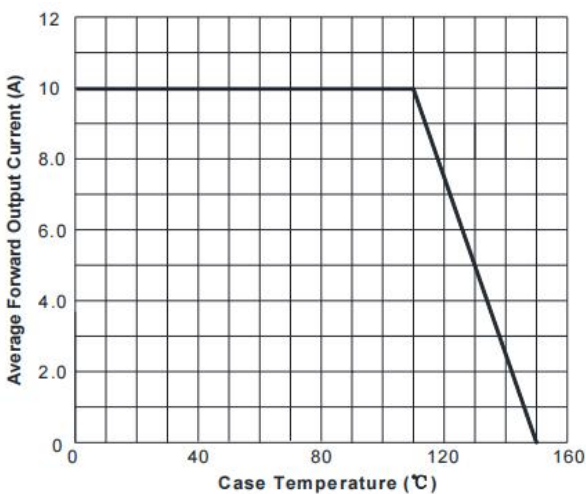


Figure 1: Forward Current Derating Curve

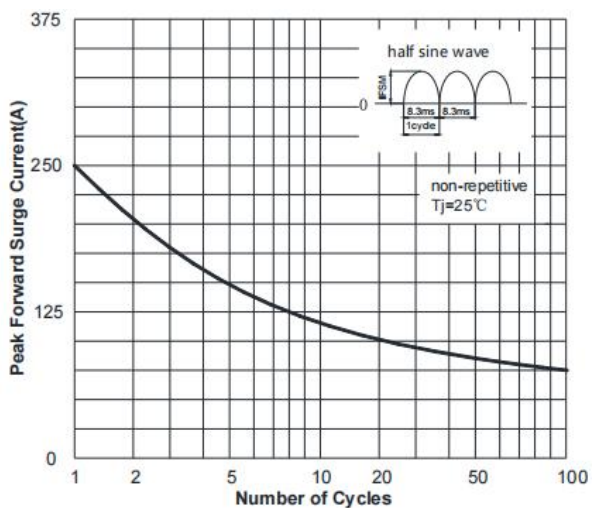


Figure 2: Peak Forward Surge Current

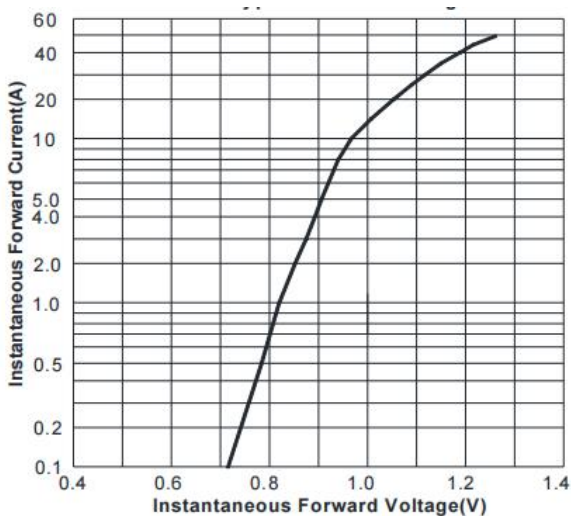


Figure 3: Instantaneous Forward Characteristics

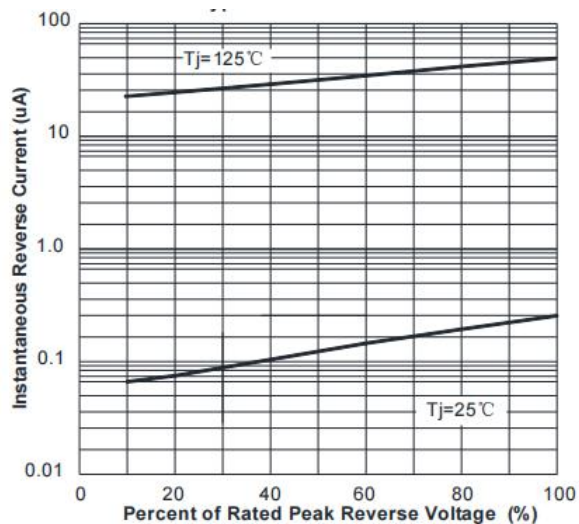
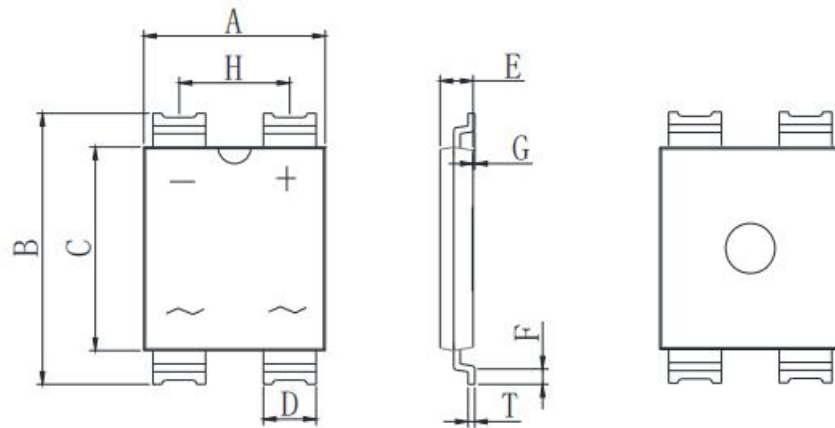


Figure 4: Reverse Leakage Characteristics

■Dimension 外形封装尺寸

YBS6



Dimensions in millimeters

YBS6		
Dim	Min	Max
A	10.70	11.30
B	15.85	16.65
C	11.70	12.30
D	3.05	3.35
E	1.80	2.20
F	0.70	1.10
G	0	0.20
H	6.55	6.85
T	0.35	0.55